

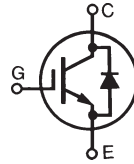
# High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

## IXBX28N300HV

$$V_{CES} = 3000V$$

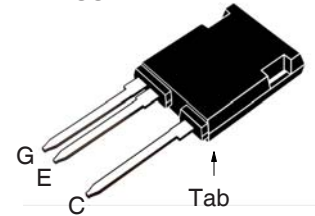
$$I_{C110} = 28A$$

$$V_{CE(sat)} \leq 2.7V$$



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	3000	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	62	A
$I_{C110}$	$T_C = 110^\circ C$	28	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	200	A
<b>SSOA</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 15\Omega$	$I_{CM} = 220$	A
<b>(RBSOA)</b>	Clamped Inductive Load	1500	V
$T_{SC}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 52\Omega$ , $V_{CE} = 1250V$ , Non-Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	350	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
$F_C$	Mounting Force	20..120/4.5..27	N/lb
<b>Weight</b>		6	g

TO-247PLUS-HV



G = Gate                      E = Emitter  
C = Collector                Tab = Collector

### Features

- High Blocking Voltage
- High Voltage Package
- Low Conduction Losses

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Uninterruptible Power Supplies (UPS)
- Switch-Mode and Resonant-Mode Power Supplies
- Capacitor Discharge Circuits
- Laser Generators

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 1 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 25V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 28A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		2.3 2.8	2.7 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 28\text{A}, V_{CE} = 10\text{V}$ , Note 1	14	24	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2370	pF
$C_{oes}$			87	pF
$C_{res}$			30	pF
$Q_{g(on)}$	$I_C = 28\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1500\text{V}$		110	nC
$Q_{ge}$			14	nC
$Q_{gc}$			50	nC
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 28\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		50	ns
$t_r$			412	ns
$t_{d(off)}$			125	ns
$t_f$			3660	ns
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 28\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		74	ns
$t_r$			805	ns
$t_{d(off)}$			245	ns
$t_f$			3280	ns
$R_{thJC}$				0.36 $^\circ\text{C}/\text{W}$
$R_{thCS}$		0.15		$^\circ\text{C}/\text{W}$

**TO-247PLUS-HV Outline**

**1 - Gate  
2,4 - Emitter  
3 - Collector**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30

### Reverse Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$V_F$	$I_F = 28\text{A}, V_{GE} = 0\text{V}$ , Note 1			2.7 V
$t_{rr}$	$I_F = 14\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GE} = 0\text{V}$		1.5	$\mu\text{s}$
$I_{RM}$			31.0	A
$Q_{RM}$			22.5	$\mu\text{C}$

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

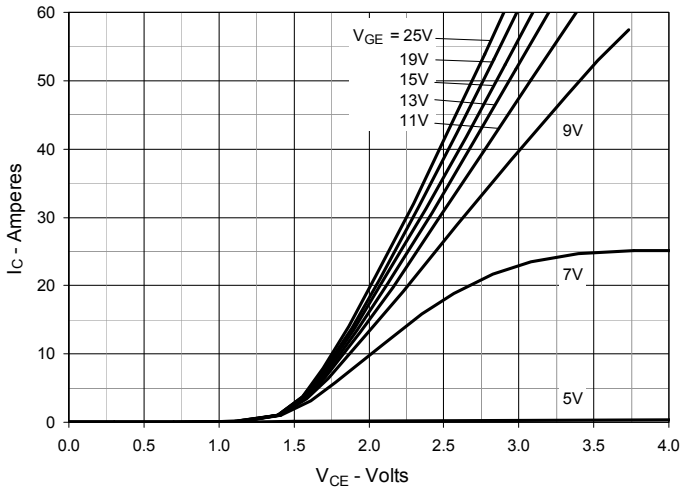
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

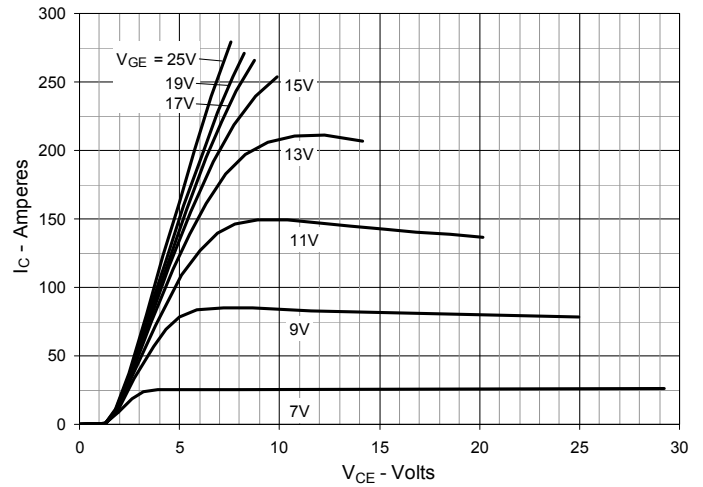
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

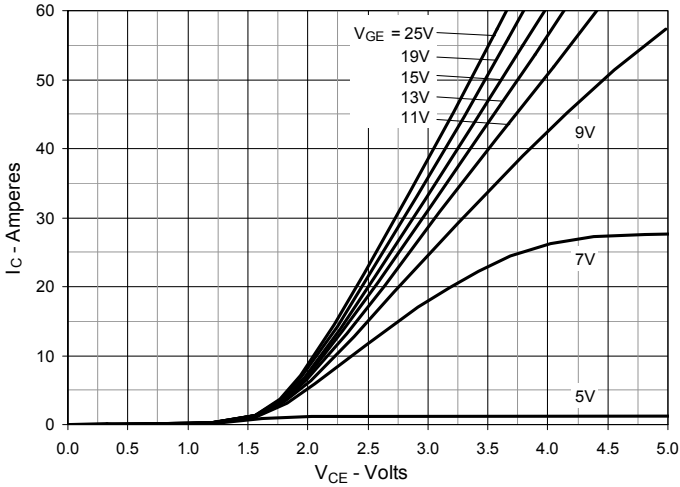
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



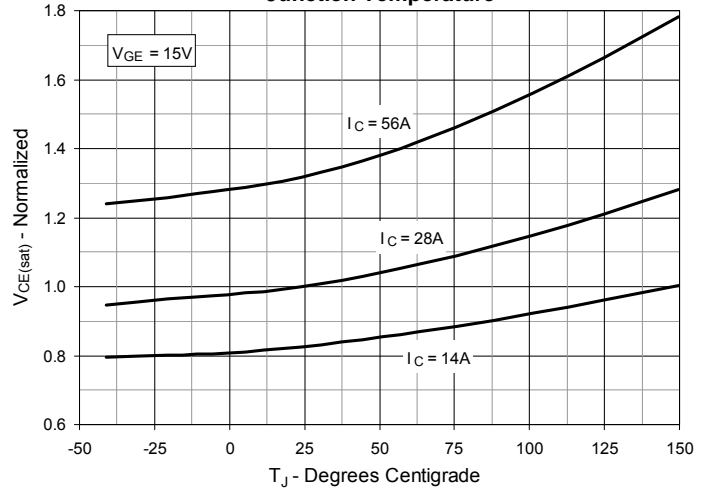
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



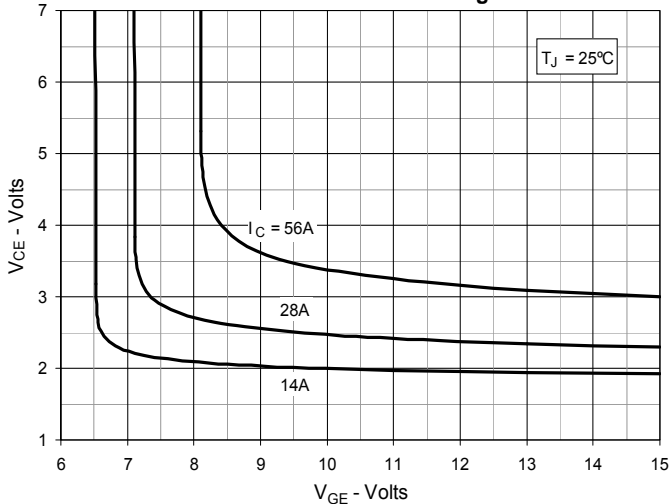
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



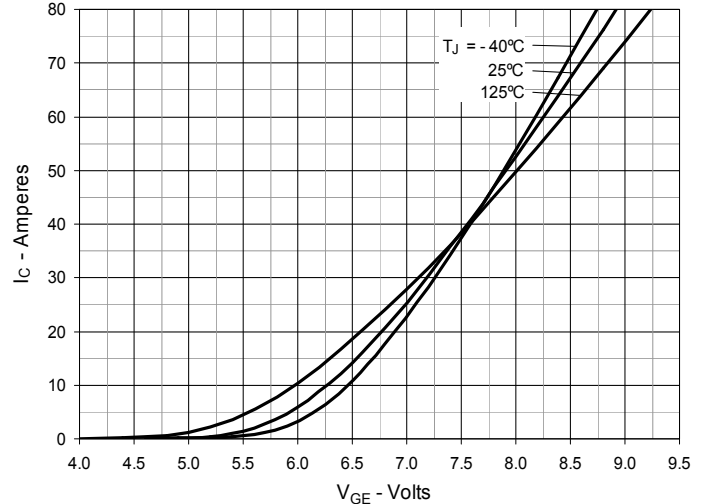
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



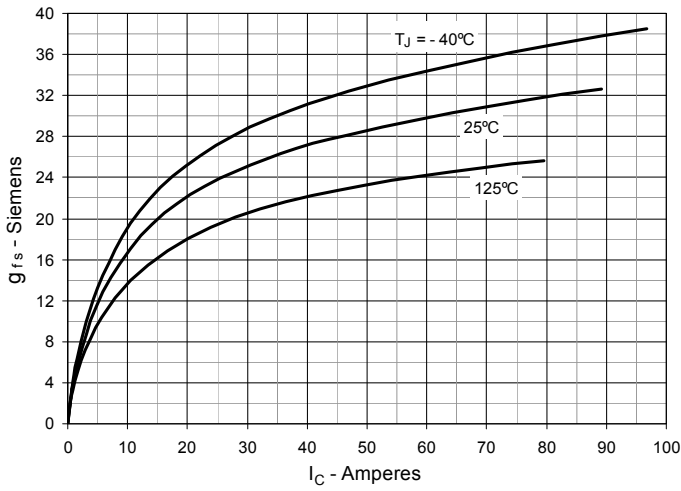
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



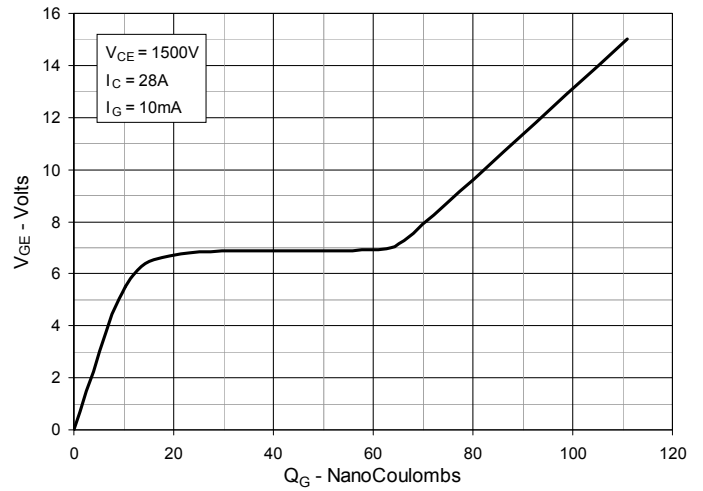
**Fig. 6. Input Admittance**



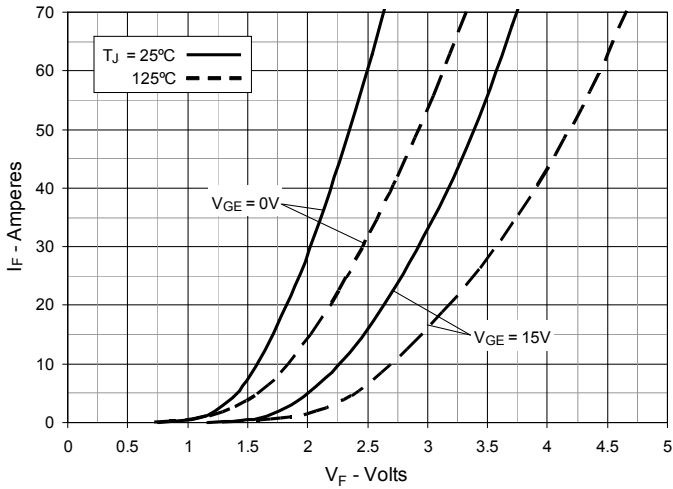
**Fig. 7. Transconductance**



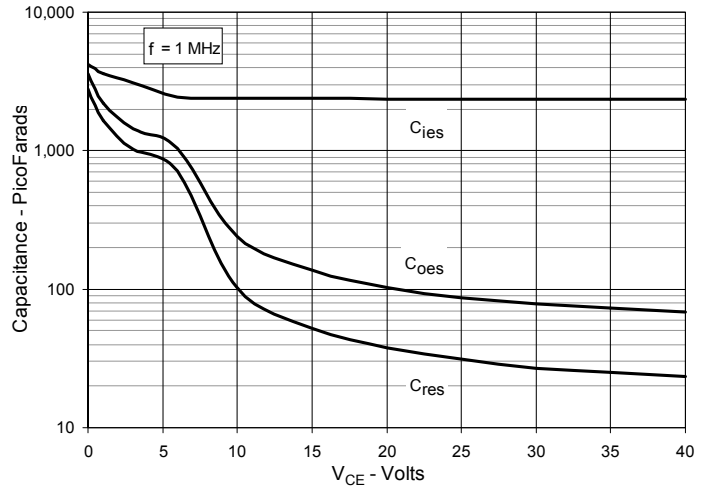
**Fig. 8. Gate Charge**



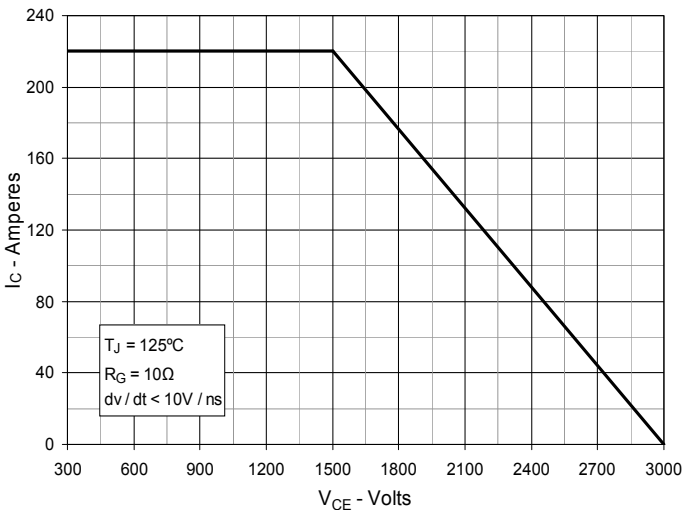
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



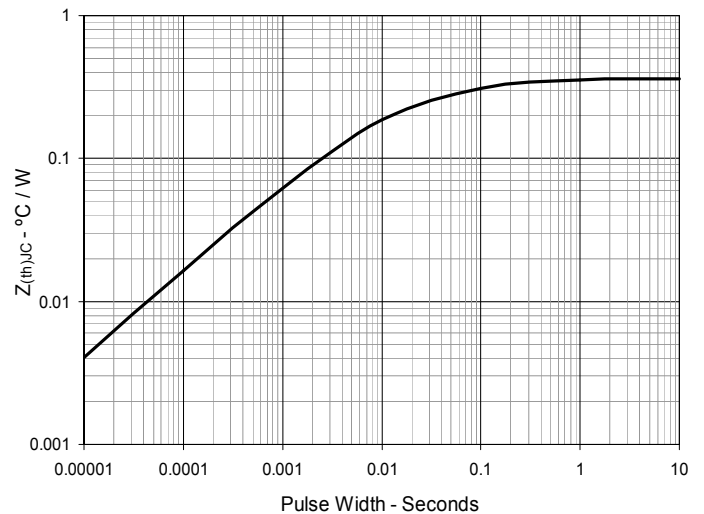
**Fig. 10. Capacitance**



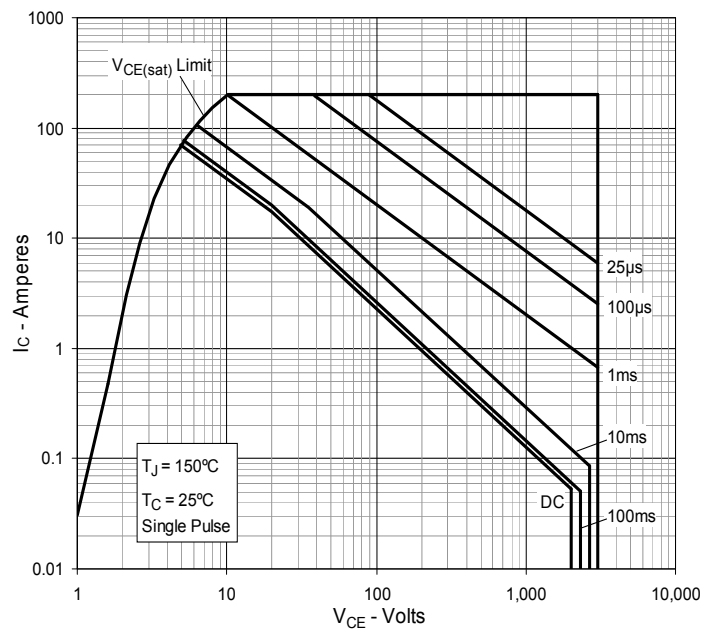
**Fig. 11. Reverse-Bias Safe Operating Area**



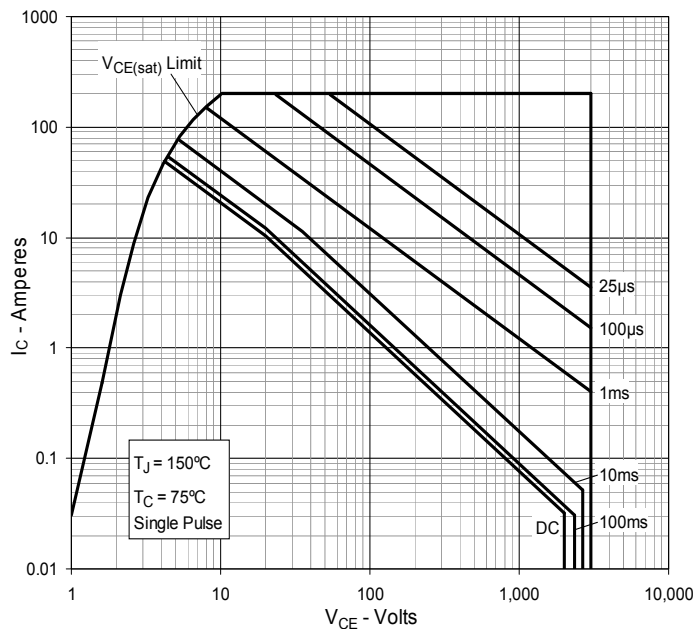
**Fig. 12. Maximum Transient Thermal Impedance**



**Fig. 13. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 14. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$**





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